

**SPECIFICATION OF LED CHIP
C750-40P
[INFRARED]**

1) Commodity Type and Physical Characteristics.

- | | | |
|----------------------|----------------------------|------------------|
| 1. Material | GaAlAs/GaAlAs (DDH) | |
| 2. Electrode | Top Side N (cathode) side | : Au Alloy & Pad |
| | Bottom Side P (anode) side | : Au Alloy |
| 3. Electrode Pattern | Fig.1 | |
| 4. Chip Size | Fig.2 | |
| 5. Chip Thickness | Fig.2 | |
| 6. Emission Area | Fig.2 | |

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=20mA		1.50	1.90	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	2.0	3.5		mW
Peak Wavelength	λ P	If=20mA		750		nm
Spectral Radiation Bandwidth	DI	If=20mA		30		nm
Rise Time	tr	If=20mA		80		ns
Full time	tf	If=20mA		80		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

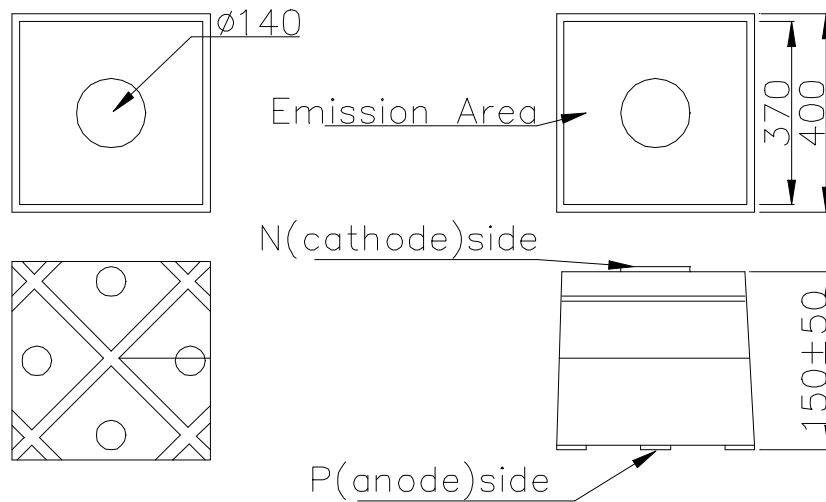


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area